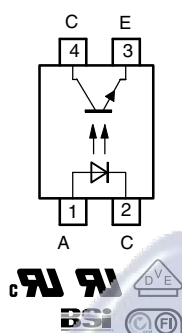
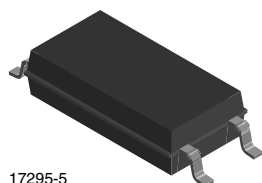


**TCLT100. Series**

Vishay Semiconductors

Optocoupler, Phototransistor Output, SOP-4L, Long Mini-Flat Package

**FEATURES**

- SMD low profile 4 lead package
- $V_{IORM} = 1050\text{ V}$
- CTR flexibility available see order information
- Special construction
- Extra low coupling capacitance
- DC input with transistor output
- Creepage distance > 8 mm



RoHS
COMPLIANT
GREEN
(5-2008)

DESCRIPTION

The TCLT100. series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4-lead SOP4L package.

APPLICATIONS

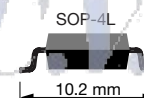
- Switchmode power supplies
- Computer peripheral interface
- Microprocessor system interface

AGENCY APPROVALS

- UL1577, file no. E76222
- CSA (cUL) 22.2 bulletin 5A recognized file no. E-76222
- BSI: BS EN 41003, BS EN 60065 (BS 415), BS EN 60950 (BS 7002), certificate number 7081 and 7402
- DIN EN 60747-5-5 (VDE 0884), available with option 1
- FIMKO (SETI): EN 60950
- CQC

Note

- See the safety standard approval list "Agency Table" for more detailed information.

ORDERING INFORMATION

AGENCY CERTIFIED/PACKAGE	CTR (%)								
	5 mA	10 mA			5 mA				
UL, cUL, VDE, BSI, FIMKO	50 to 600	63 to 125	100 to 200	160 to 320	50 to 150	100 to 300	80 to 160	130 to 260	200 to 400
SOP-4L	TCLT1000	TCLT1002	TCLT1003	TCLT1004	TCLT1005	TCLT1006	TCLT1007	TCLT1008	TCLT1009

Note

- Available only on tape and reel.

**TCLT100. Series**

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10\text{ }\mu\text{s}$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10\text{ ms}$	I_{CM}	100	mA
Power dissipation		P_{diss}	150	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
COUPLER				
Isolation test voltage (RMS)		V_{ISO}	5000	V_{RMS}
Total power dissipation		P_{tot}	250	mW
Operating ambient temperature range		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 55 to + 125	$^{\circ}\text{C}$
Soldering temperature		T_{slid}	260	$^{\circ}\text{C}$

Note

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50\text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1\text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100\text{ }\mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20\text{ V}, I_F = 0\text{ A}$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10\text{ mA}, I_C = 1\text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}, R_L = 100\text{ }\Omega$	f_c		110		kHz
Coupling capacitance	$f = 1\text{ MHz}$	C_k		0.3		pF

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



TCLT100. Series

Vishay Semiconductors

CURRENT TRANSFER RATIO ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCLT1000	CTR	50		600	%
		TCLT1002	CTR	63		125	%
	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}$	TCLT1003	CTR	100		200	%
		TCLT1004	CTR	160		320	%
	$V_{CE} = 5\text{ V}, I_F = 1\text{ mA}$	TCLT1002	CTR	22	45		%
		TCLT1003	CTR	34	70		%
		TCLT1004	CTR	56	100		%
	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCLT1005	CTR	50		150	%
		TCLT1006	CTR	100		300	%
		TCLT1007	CTR	80		160	%
		TCLT1008	CTR	130		260	%
		TCLT1009	CTR	200		400	%

SAFETY AND INSULATION RATED PARAMETERS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{test} = 1\text{ s}$	V_{pd}	2			kV
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60\text{ s}, t_{test} = 10\text{ s}$, (see figure 2)	V_{IOTM}			8	kV _{peak}
		V_{pd}			1.68	kV _{peak}
Insulation resistance	$V_{IO} = 500\text{ V}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ }^{\circ}\text{C}$	R_{IO}	10^{11}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 150\text{ }^{\circ}\text{C}$ (construction test only)	R_{IO}	10^9			Ω
Forward current		I_{si}	130			mA
Power dissipation		P_{so}	265			mW
Rated impulse voltage		V_{IOTM}	8			kV
Safety temperature		T_{si}	150			$^{\circ}\text{C}$
Clearance distance			8.0			mm
Creepage distance			8.0			mm
Insulation distance (internal)			0.40			mm

Note

- According to DIN EN 60747-5-2 (VDE 0884) (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

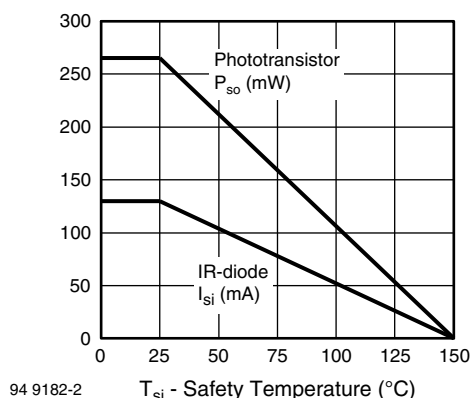


Fig. 1 - Derating Diagram

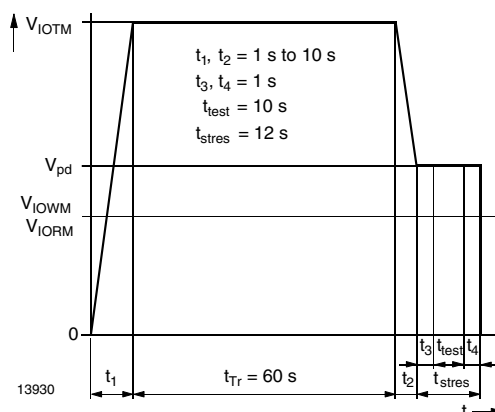


Fig. 2 - Test Pulse Diagram for Sample Test according to DIN EN 60747-5-2 (VDE 0884); IEC60747-5-5



TCLT100. Series

Vishay Semiconductors

SWITCHING CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_d		3		μs
Rise time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_r		3		μs
Fall time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_f		4.7		μs
Storage time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_{on}		6		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$, (see figure 3)	t_{off}		5		μs
Turn-on time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{on}		9		μs
Turn-off time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{off}		10		μs

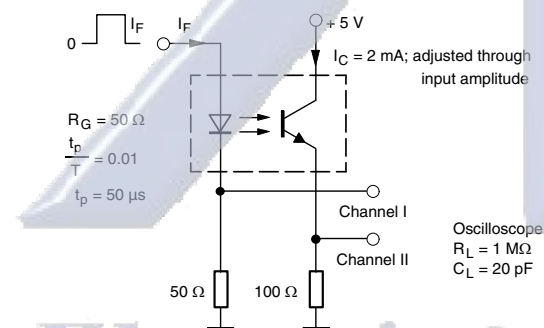


Fig. 3 - Test Circuit, Non-Saturated Operation

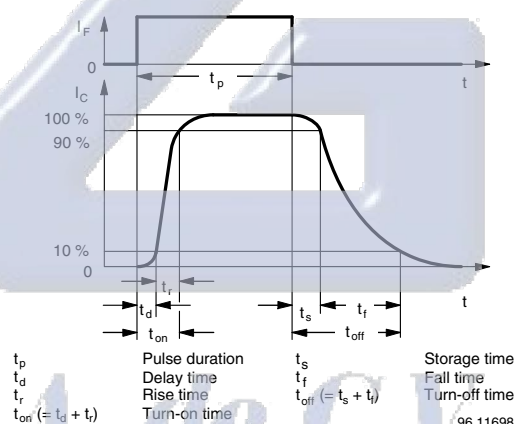


Fig. 5 - Switching Times

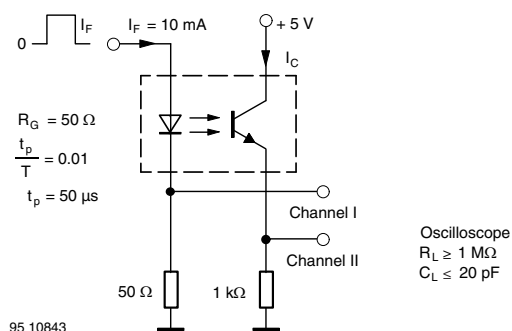
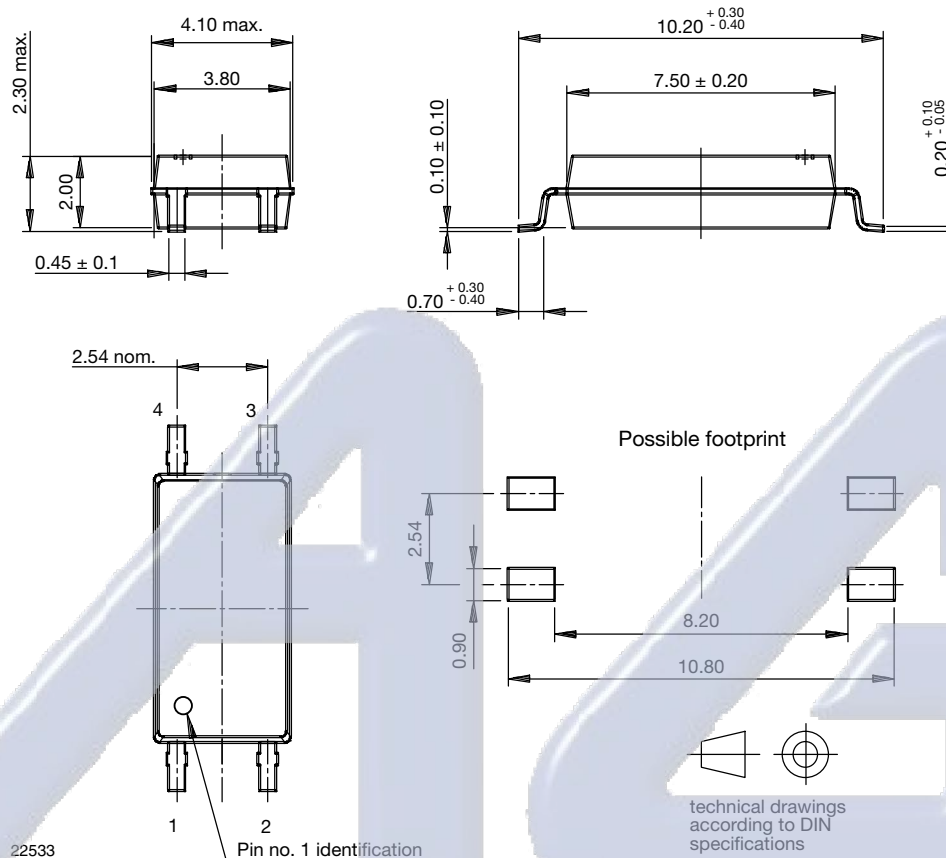


Fig. 4 - Test Circuit, Saturated Operation

**TCLT100. Series**

Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters**PACKAGE MARKING**